

40V NPN MEDIUM POWER PLANAR TRANSISTOR IN SOT23

Features and Benefits

- BV_{CEO} > 40V
- I_C = 4A Continuous Collector Current
- Low Saturation Voltage V_{CE(sat)} < 55mV @ 1A
- $R_{CE(sat)} = 35m\Omega$
- h_{FE} characterised up to 10A
- High h_{FE} min 300 @ 1A
- 1.25W power dissipation
- 130V forward blocking voltage
- 6V reverse blocking voltage
- Complementary part number ZXTP25040DFH
- "Lead-Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

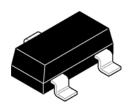
Mechanical Data

- Case: SOT23
- Case material: Molded Plastic. "Green" Molding Compound (Note 2) UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

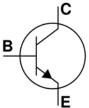
Applications

- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters

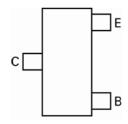
SOT23



Top View



Device Symbol



Top View Pin Configuration

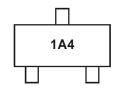
Ordering Information (Note 3)

	Product Marking		Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXT	N25040DFHTA	1A4	7	8	3,000	

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" Policy can be found on our website at https://www.diodes.com/
- 3. Devices with lot number starting from PID0155145 (March 2010) are "Green" products.

Marking Information



1A4 = Product Type Marking Code





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	;	Symbol	Value	Unit	
Collector-Base Voltage		V_{CBO}	130	V	
Collector-Emitter Voltage (Forward Blocki	ng)	V _{CEX}	130	V	
Collector-Emitter Voltage		V _{CEO}	40	V	
Emitter-Collector Voltage (Reverse Blocking)		V _{ECO}	6	V	
Emitter-Base Voltage		V_{EBO}	7	V	
Continuous Collector Current	(Note 6)	Ic	4	А	
Peak Pulse Current		Ісм	10	А	
Base Current		I _B	1	А	

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
	(Note 4)		0.73 5.84		
Power Dissipation	(Note 5)	P _D -	1.05 8.4	w	
Linear Derating Factor	(Note 6)		1.25 9.6	mW/°C	
	(Note 7)		1.81 14.5		
	(Note 4)		171		
Thermal Desistance Investigate Archient	(Note 5)		119	20044	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	100	°C/W	
	(Note 7)		69		
Thermal Resistance, Junction to Lead (Note 8)		$R_{ heta JL}$	74.95	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

Notes:

- 4. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 5. For a device surface mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. For a device surface mounted on 50mm X 50mm X 1.6mm FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

 7. As note 6 above, measured at t < 5 seconds

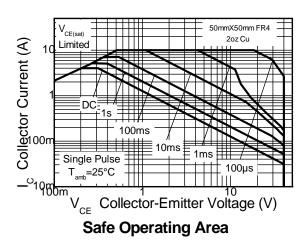
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).



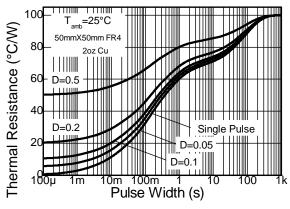
Failure may occur

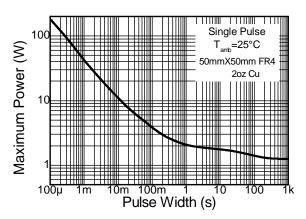
ZXTN25040DFH

Typical Thermal Characteristics



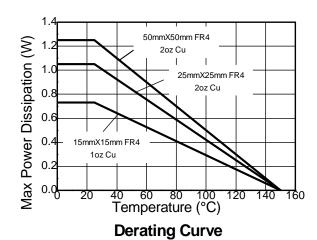
Safe Operating Area





Transient Thermal Impedance

Pulse Power Dissipation







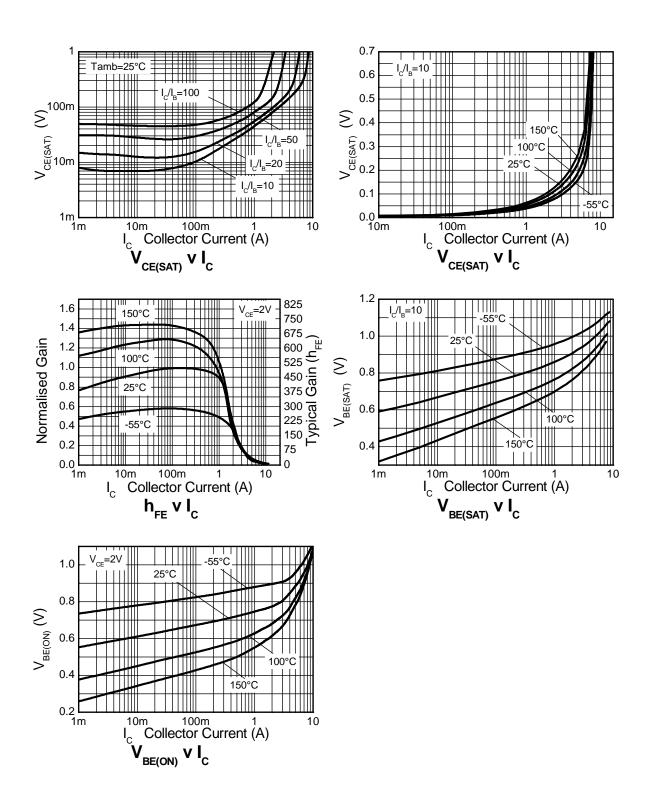
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	BV_CBO	130	170	-	V	$I_C = 100\mu A$		
Collector-emitter breakdown voltage (forward blocking)	BV _{CEX}	130	170	-	V	I_C = 100μA; R_{BE} < 1k Ω or -1V < V_{BE} < 0.25V		
Collector-Emitter Breakdown Voltage (base open) (Note 9)	BV _{CEO}	40	63	-	V	I _C = 10mA		
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	-	V	$I_E = 100\mu A$		
Emitter-collector breakdown voltage (reverse blocking)	BV _{ECX}	6	7.4	-	V	$I_E = 100 \mu A$; $R_{BC} < 1 k \Omega$ or $-0.25 V < V_{BC} < 0.25 V$		
Emitter-collector breakdown voltage (base open)	BV_{ECO}	6	7.4	-	V	I _E = 100μA;		
Collector-base Cut-off Current	I _{CBO}	-	<1 -	50 20	nΑ μΑ	V _{CB} = 100V V _{CB} = 100V, T _A = 100°C		
Collector-emitter Cut-off Current	I _{CEX}	-	-	100	nA	$V_{CE} = 100V; R_{BE} < 1k\Omega \text{ or}$ -1V < $V_{BE} < 0.25V$		
Emitter-base Cut-off Current	I _{EBO}	-	<1	50	nA	V _{EB} = 5.6V		
ON CHARACTERISTICS (Note 9)						_		
Static Forward Current Transfer Ratio	h _{FE}	300 300 30 -	450 450 60 10	900	-	$I_C = 10mA$, $V_{CE} = 2V$ $I_C = 1A$, $V_{CE} = 2V$ $I_C = 4A$, $V_{CE} = 2V$ $I_C = 10A$, $V_{CE} = 2V$		
Collector-Emitter Saturation Voltage	VCE(sat)	-	45 120 135 140	55 210 210 190	mV	$I_C = 1A$, $I_B = 100mA$ $I_C = 1A$, $I_B = 10mA$ $I_C = 2A$, $I_B = 40mA$ $I_C = 4A$, $I_B = 400mA$		
Base-Emitter Saturation Voltage	V _{BE(sat)}	-	960	1050	mV	$I_C = 4A$, $I_B = 400mA$		
Base-Emitter On Voltage	$V_{BE(on)}$	-	840	950	mV	$I_C = 4A$, $V_{CE} = 2V$		
SMALL SIGNAL CHARACTERISTICS (Note 9)				1				
Transition Frequency	f⊤	-	190	-	MHz	I _C = 50mA, V _{CE} = 10V, f = 100MHz		
Collector Output Capacitance	C_{obo}	-	11.7	20	pF	V _{CB} = 10V, f = 1MHz		
Delay time	t _d	-	64	-	ns	101/		
Rise time	t _r	-	108	-	ns	$V_{CC} = 10V$, $I_{C} = 1A$.		
Storage time	t _s	-	428	-	ns	$-I_{B1} = I_{B2} = 10$ mA		
Fall time	t _f	-	130	-	ns	161 - 162 - 1011174		

Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

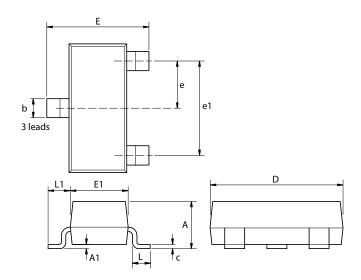


Typical Electrical Characteristics





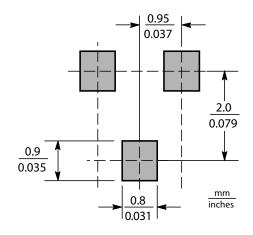
Package Outline Dimensions



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95 NOM		0.037	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Suggested Pad Layout







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